

SANYO

No.924E

2SB880/2SD1190Silicon PNP/NPN Epitaxial Planar Type
Darlington Transistor
FOR VARIOUS DRIVERS**Applications**

- Motor drivers, printer hammer drivers, relay drivers, voltage regulators

Features

- High DC current gain
- Large current capacity and wide ASO
- Low saturation voltage

(): 2SB880

Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$

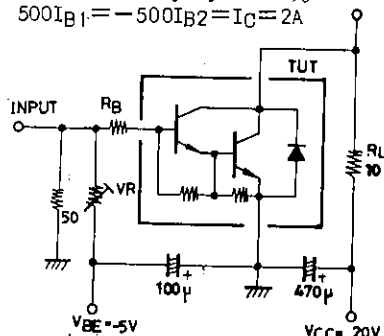
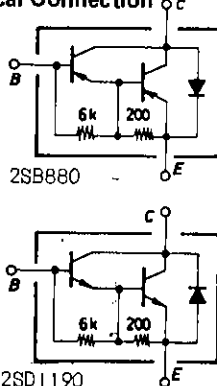
Collect-to-Base Voltage	V_{CBO}	(-)70	V
Collector-to-Emitter Voltage	V_{CEO}	(-)60	V
Emitter-to-Base Voltage	V_{EBO}	(-)6	V
Collector Current	I_C	(-)4	A
Peak Collector Current	i_{cp}	(-)6	A
Collector Dissipation	P_C	1.75	W
	$T_c=25^{\circ}\text{C}$	30	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature	T_{sta}	-55 to +150	$^{\circ}\text{C}$

Electrical Characteristics/ $T_a=25^\circ\text{C}$

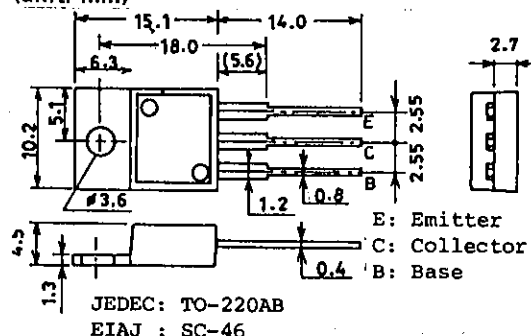
			min	typ	max	unit
Collector Cut-off Current	I_{CBO}	$V_{CB}=(-)40, I_E=0$			(-)0.1	mA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$			(-)3.0	mA
DC Current Gain	h_{FE}	$V_{CE}=(-)2V, I_C=(-)2A$	2000	5000		
Gain Band-width Product	f_T	$V_{CE}=(-)5V, I_C=(-)2A$		20		MHz
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)2A, I_B=(-)4mA$		0.9 (-1.0)	(-)1.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)2A, I_B=(-)4mA$			(-)2.0	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)5mA, I_E=0$	(-)70			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)50mA, R_{BE}=\infty$	(-)60			V
Turn-on Time	t_{on}	At Specified Test Circuit		(0.5)0.6		μs
Storage Time	t_{stg}	"		(1.4)2.7		μs
Fall Time	t_f	"		(1.2)1.6		μs

Specified Test Circuit

(For PNP, the polarity is reversed.)

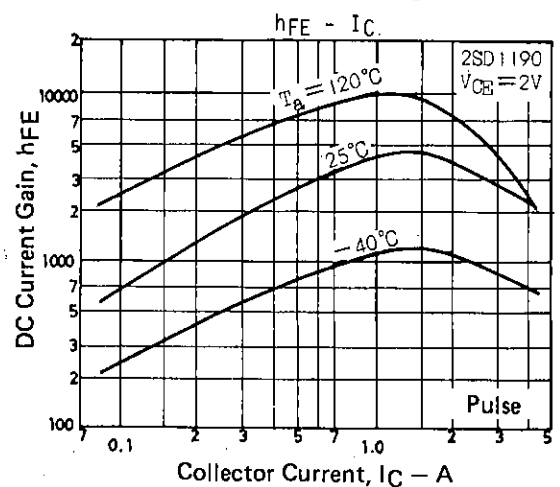
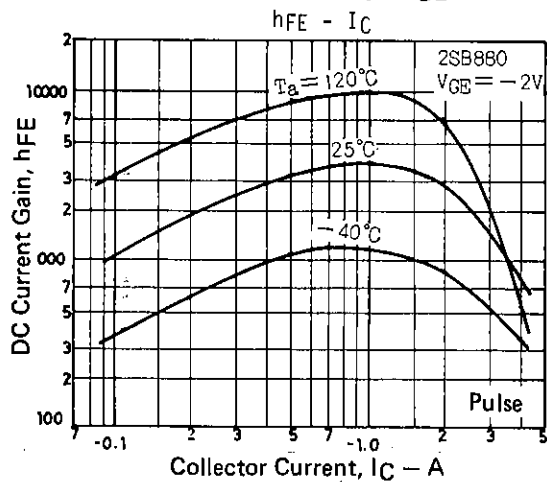
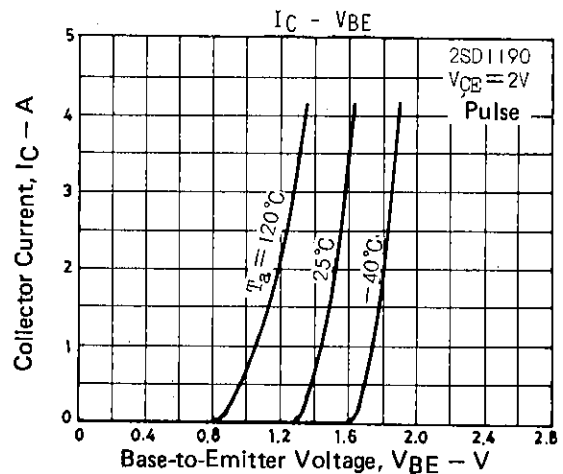
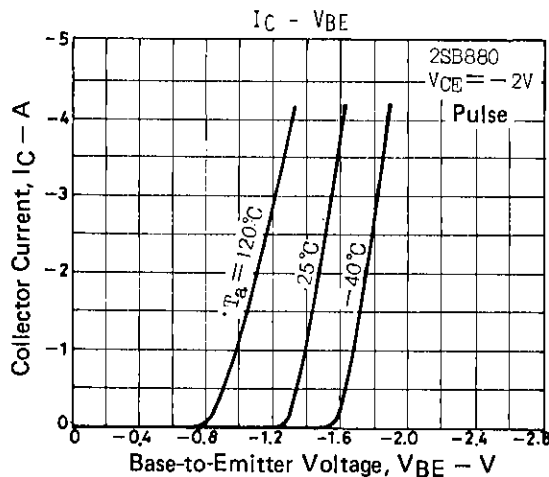
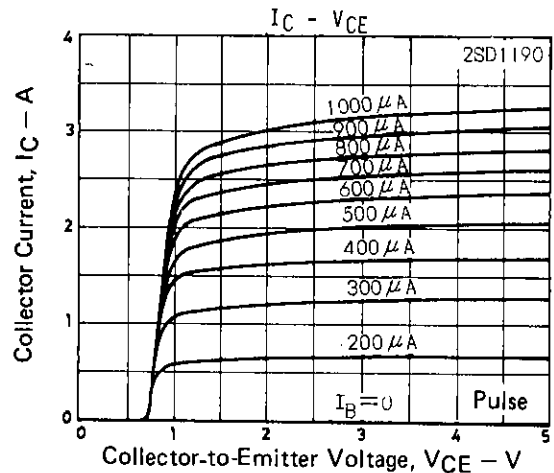
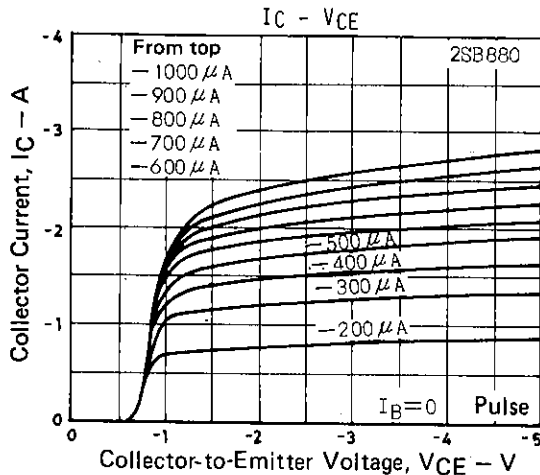
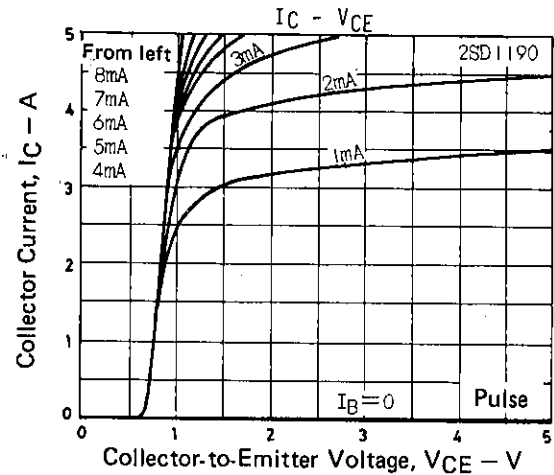
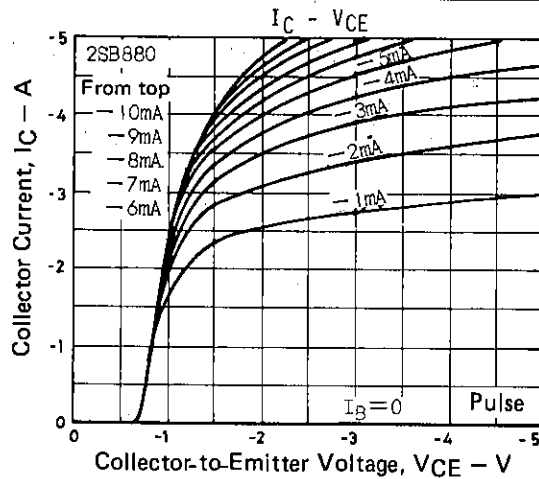
 $PW=50\mu\text{s}$, Duty Cycle $\leq 1\%$
 $500I_{B1}=-500I_{B2}=I_C=2A$
**Electrical Connection****Package Dimensions 2010B**

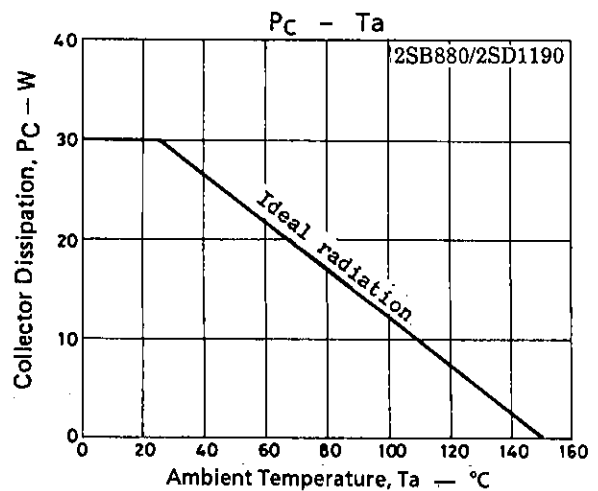
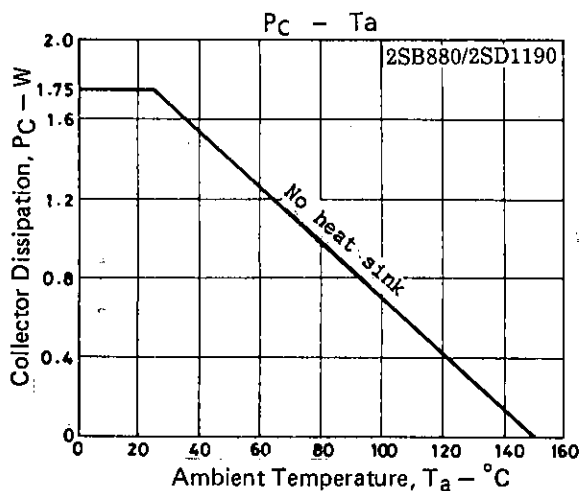
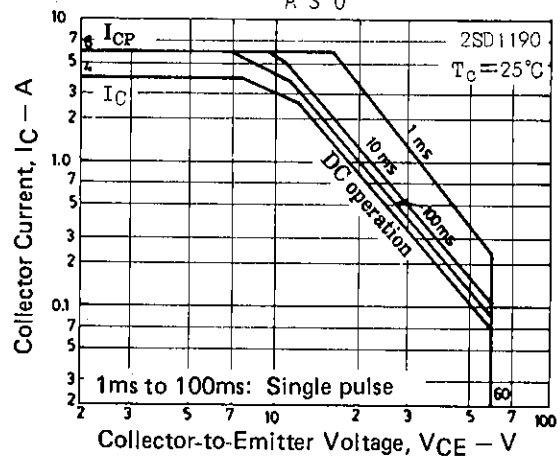
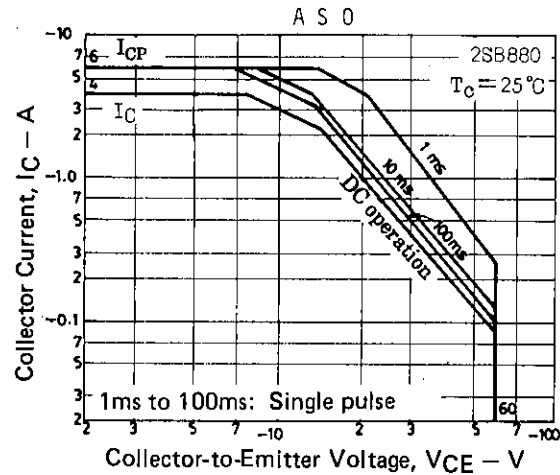
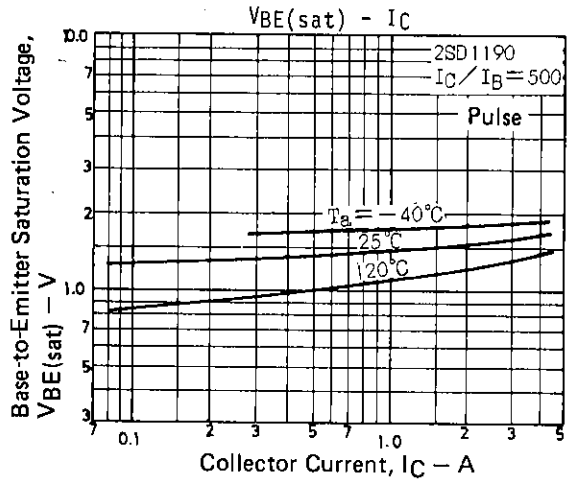
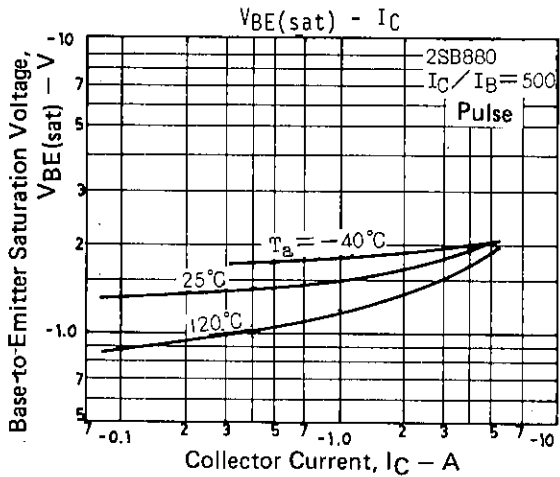
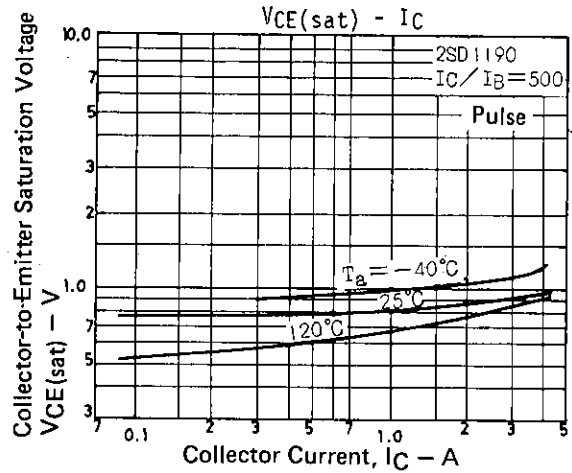
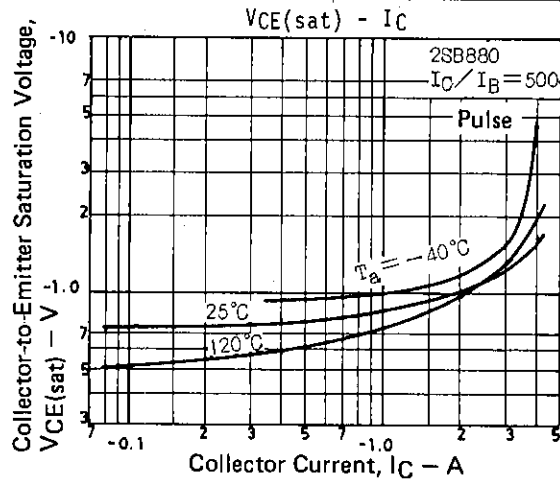
(unit: mm)

Unit (resistance: Ω , capacitance: F)

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D251MH/4027KI/2033KI, TS №924-1/4





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